

Description

The AO6802 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

VDS = 30V ID = 4.5A

 $R_{DS(ON)} < 38m\Omega @ V_{GS}=10 V$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

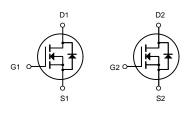
Product ID	Pack	Brand	Qty(PCS)
AO6802	SOT-23-6L	HXY MOSFET	3000

Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	<u>+</u> 12	V
I₀@T₄=25℃	Drain Current, V _{GS} @ 4.5V ³	4.5	А
Ідм	Pulsed Drain Current ¹	15	А
P _D @T _A =25°C	Total Power Dissipation	1.25	W
Тята	Storage Temperature Range	-55 to 150	°C
Tj	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	125	°C/W



SOT-23-6L



Dual N-Channel MOSFET



Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250µA	30	-	-	V
DSS	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.5	V
D	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =4A	-	29	38	mΩ
$R_{DS(on)}$		V _{GS} =4.5V, I _D =3A	-	45	65	
Ciss	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	233	-	pF
Coss	Output Capacitance		-	44	-	pF
Crss	Reverse Transfer Capacitance		-	33	-	pF
Q_{g}	Total Gate Charge	- V _{DS} =15V, I _D =2A, - V _{GS} =10V	-	3	-	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	nC
Q_gd	Gate-Drain("Miller") Charge		-	0.8	-	nC
t _{d(on)}	Turn-on Delay Time		-	4	-	ns
tr	Turn-on Rise Time	V _{DS} =15V,	-	2.1	-	ns
t _{d(off)}	Turn-off Delay Time	$I_D=4A, R_{GEN}=3\Omega,$	-	15	-	ns
t _f	Turn-off Fall Time	V _{GS} =10V	-	3.2	-	ns
ls	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.5	А
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	А
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4A	-	-	1.2	V

Electrical Characteristics (T_J=25°C unless otherwise specified)

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



Typical Performance Characteristics

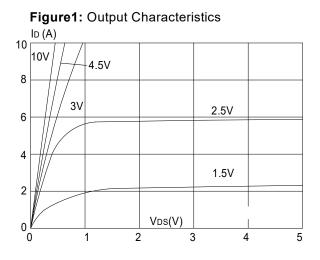
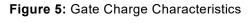
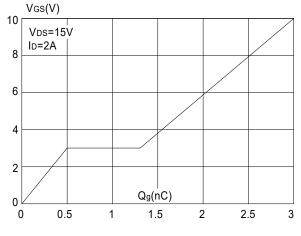


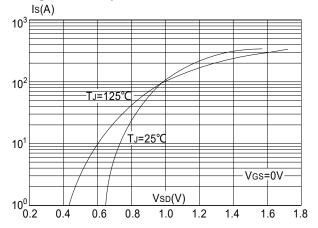
Figure 3: On-resistance vs. Drain Current $RDS(ON)(m\Omega)$ 60 50 Vgs=4.5V 40 30 Vgs=10V 20 ID(A) 10 2 3 5 1 4 0

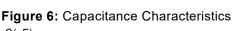




25 [D (A) 20 15 12⁵℃ 10 25℃ 5 ∕VGs(V) 0 0 1.0 2.0 3.0 4.0 5.0 6.0

Figure 2: Typical Transfer Characteristics





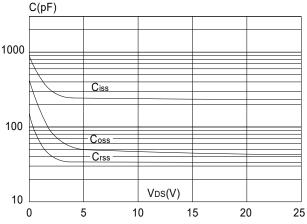


Figure 4: Body Diode Characteristics



Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

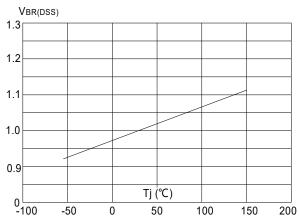


Figure 9: Maximum Safe Operating Area

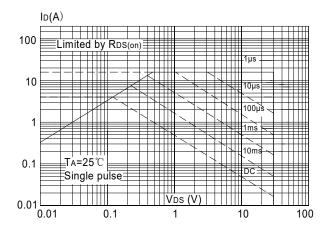


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

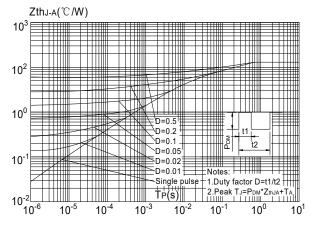


Figure 8: Normalized on Resistance vs. Junction Temperature

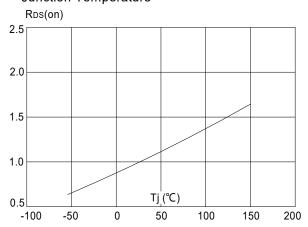
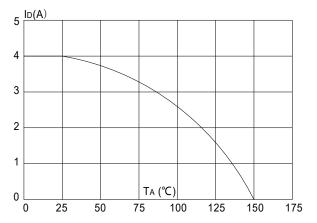
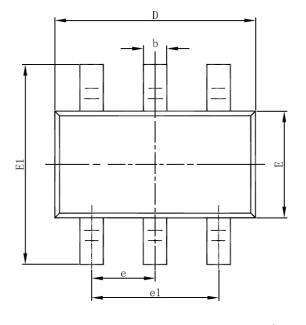


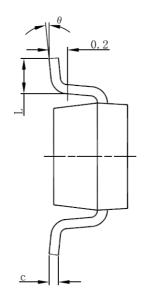
Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

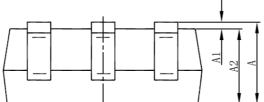




SOT-23-6L Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
А	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
Е	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



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